	Application No.	Applicant(s)
Notice of Allowability	10/530,519	IWATA ET AL.
	Examiner	Art Unit
	Mursalin B. Hafiz	2814
- The MAILING DATE of this communication appears on the cover sheet with the correspondence address All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.		
1. This communication is responsive to 6/13/06.		
2. The allowed claim(s) is/are <u>1-12</u> .		
3.		
each sheet. Replacement sheet(s) should be labeled as such in t 6. DEPOSIT OF and/or INFORMATION about the depo attached Examiner's comment regarding REQUIREMENT	sit of BIOLOGICAL MATERIAL	. must be submitted. Note the
 Attachment(s) 1. ☒ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☒ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 4/7/05 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material 	6. ☐ Interview Summa Paper No./Mail D 08), 7. ☑ Examiner's Amen	Date

Election/Restrictions

Claims 1-6, 9, and 10 are directed to an allowable product. Pursuant to the procedures set forth in MPEP § 821.04(b), claim7,8, 11, and 12, are directed to species of the allowable product, previously withdrawn from consideration as a result of a restriction requirement, is hereby rejoined and fully examined for patentability under 37 CFR 1.104.

Because a claimed invention previously withdrawn from consideration under 37 CFR 1.142 has been rejoined, the restriction requirement having embodiments 1-8 as set forth in the Office action mailed on May 17, 2006 is hereby withdrawn. In view of the withdrawal of the restriction requirement as to the rejoined inventions, applicant(s) are advised that if any claims including all the limitations of an allowable product claim or rejoined process claim are presented in a continuation or divisional application, such claims may be subject to provisional statutory and/or nonstatutory double patenting rejections over the claims of the instant application. Once the restriction requirement is withdrawn, the provisions of 35 U.S.C. 121 are no longer applicable. See *In re Ziegler*, 443 F.2d 1211, 1215, 170 USPQ 129, 131-32 (CCPA 1971). See also MPEP § 804.01.

EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

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The application has been amended as follows:

In the claims:

In claims 1-12, delete all the label numerals (such as: claim 1 line 2, semiconductor part "(11, 111, 111a, 72, 189)" composed should be: --semiconductor part composed--).

In the Specification:

Change the title to: --SEMICONDUCTOR STORAGE DEVICE HAVING A
FUNCTION TO CONVERT CHANGES OF AN ELECTRIC CHARGE AMOUNT TO A
CURRENT AMOUNT--.

Change the abstract to: (See the attachment)

Allowable Subject Matter

Claims 1-12 are allowed.

The following is an examiner's statement of reasons for allowance:

Prior art does not teach, the charge holding portion are each constructed so as to change, in accordance with an electric charge amount held in the charge holding portions, a current amount flowing from one of the second conductivity type diffusion layer region to the other of the diffusion layer region through the channel region when a voltage is applied to the gate electrode and part of each charge holding portion is resent below an interface of the gate insulating film and the channel region in combination with other limitations of the claim.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably

accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Mursalin B. Hafiz whose telephone number is 571-272-8604. The examiner can normally be reached on m-f 9-5.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on 571-272-1705. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Mbh

HOAI 'PHAM PRIMARY EXAMINER Art Unit: 2814

ABSTRACT

In a semiconductor storage device, a gate insulating film and a gate electrode are laid on a first conductivity type semiconductor substrate, and charge holding portions are formed on both sides of the gate electrode. Second conductivity type first and second diffusion layer regions are formed in regions of the semiconductor substrate corresponding to the charge holding portions. The charge holding portions are each structured so as to change, in accordance with an electric charge amount held in the charge holding portions, a current amount flowing from one of the second conductivity type diffusion layer regions to the other of the diffusion layer regions through a channel region when voltage is applied to the gate electrode. Part of each charge holding portion is present below an interface of the gate insulating film and the channel region.